



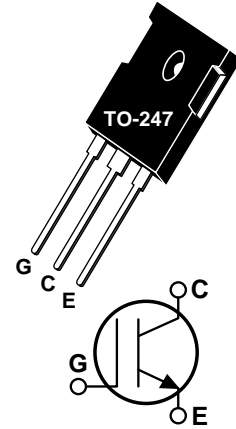
**THE DATASHEET OF
APT20GF120BRG**



Fast IGBT

The Fast IGBT is a new generation of high voltage power IGBTs. Using Non-Punch Through Technology the Fast IGBT offers superior ruggedness, fast switching speed and low Collector-Emitter On voltage.

- Low Forward Voltage Drop
- Low Tail Current
- Avalanche Rated
- High Freq. Switching to 20KHz
- Ultra Low Leakage Current
- RBSOA and SCSOA Rated




MAXIMUM RATINGS

All Ratings: $T_C = 25^\circ\text{C}$ unless otherwise specified.

Symbol	Parameter	APT20GF120BR	UNIT
V_{CES}	Collector-Emitter Voltage	1200	Volts
V_{CGR}	Collector-Gate Voltage ($R_{GE} = 20K\Omega$)	1200	
V_{GE}	Gate-Emitter Voltage	± 20	
I_{C1}	Continuous Collector Current @ $T_C = 25^\circ\text{C}$	32	Amps
I_{C2}	Continuous Collector Current @ $T_C = 90^\circ\text{C}$	20	
I_{CM}	Pulsed Collector Current ^① @ $T_C = 25^\circ\text{C}$	64	
I_{LM}	RBSOA Clamped Inductive Load Current @ $R_g = 11\Omega$ $T_C = 125^\circ\text{C}$	40	
E_{AS}	Single Pulse Avalanche Energy ^②	22	mJ
P_D	Total Power Dissipation	200	Watts
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to 150	$^\circ\text{C}$
T_L	Max. Lead Temp. for Soldering: 0.063" from Case for 10 Sec.	300	

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT
BV_{CES}	Collector-Emitter Breakdown Voltage ($V_{GE} = 0V, I_C = 0.8mA$)	1200			Volts
$V_{GE(TH)}$	Gate Threshold Voltage ($V_{CE} = V_{GE}, I_C = 350\mu A, T_J = 25^\circ\text{C}$)	4.5	5.5	6.5	
$V_{CE(ON)}$	Collector-Emitter On Voltage ($V_{GE} = 15V, I_C = 15A, T_J = 25^\circ\text{C}$)		2.7	3.2	
	Collector-Emitter On Voltage ($V_{GE} = 15V, I_C = 15A, T_J = 125^\circ\text{C}$)		3.3	3.9	
I_{CES}	Collector Cut-off Current ($V_{CE} = V_{CES}, V_{GE} = 0V, T_J = 25^\circ\text{C}$)			0.8	mA
	Collector Cut-off Current ($V_{CE} = V_{CES}, V_{GE} = 0V, T_J = 125^\circ\text{C}$)			5.0	
I_{GES}	Gate-Emitter Leakage Current ($V_{GE} = \pm 20V, V_{CE} = 0V$)			± 100	nA

 **CAUTION:** These Devices are Sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

APT Website - <http://www.advancedpower.com>

DYNAMIC CHARACTERISTICS

APT20GF120BR

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
C _{ies}	Input Capacitance	Capacitance V _{GE} = 0V V _{CE} = 25V f = 1 MHz		1050	1210	pF
C _{oes}	Output Capacitance			100	150	
C _{res}	Reverse Transfer Capacitance			63	110	
Q _g	Total Gate Charge ^③	Gate Charge V _{GE} = 15V V _{CC} = 0.5V _{CES} I _C = I _{C2}		95	140	nC
Q _{ge}	Gate-Emitter Charge			13	20	
Q _{gc}	Gate-Collector ("Miller") Charge			62	90	
t _{d(on)}	Turn-on Delay Time	Resistive Switching (25°C) V _{GE} = 15V V _{CC} = 0.5V _{CES} I _C = I _{C2} R _G = 10Ω		15	30	ns
t _r	Rise Time			67	130	
t _{d(off)}	Turn-off Delay Time			92	140	
t _f	Fall Time			93	190	
t _{d(on)}	Turn-on Delay Time	Inductive Switching (150°C) V _{CLAMP(Peak)} = 0.66V _{CES} V _{GE} = 15V I _C = I _{C2} R _G = 10Ω T _J = +150°C		17	34	ns
t _r	Rise Time			30	60	
t _{d(off)}	Turn-off Delay Time			105	160	
t _f	Fall Time			71	140	
E _{on}	Turn-on Switching Energy	R _G = 10Ω T _J = +150°C		1.3	3.0	mJ
E _{off}	Turn-off Switching Energy			1.5	3.0	
E _{ts}	Total Switching Losses			2.7	5.0	
t _{d(on)}	Turn-on Delay Time	Inductive Switching (25°C) V _{CLAMP(Peak)} = 0.66V _{CES} V _{GE} = 15V I _C = I _{C2} R _G = 10Ω T _J = +25°C		17	30	ns
t _r	Rise Time			35	70	
t _{d(off)}	Turn-off Delay Time			93	140	
t _f	Fall Time			70	140	
E _{ts}	Total Switching Losses			2.4	5.0	
g _{fe}	Forward Transconductance	V _{CE} = 20V, I _C = I _{C2}		12		S

THERMAL AND MECHANICAL CHARACTERISTICS

Symbol	Characteristic	MIN	TYP	MAX	UNIT
R _{θJC}	Junction to Case			0.63	°C/W
R _{θJA}	Junction to Ambient			40	
W _T	Package Weight		0.22		oz
			6.1		gm
Torque	Mounting Torque (using a 6-32 or 3mm Binding Head Machine Screw)			10	lb•in
				1.1	N•m

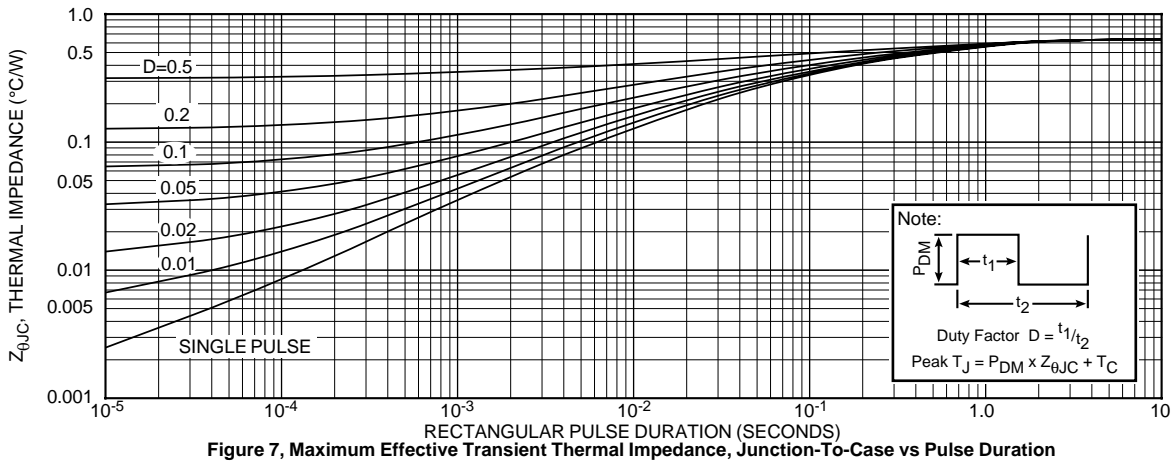
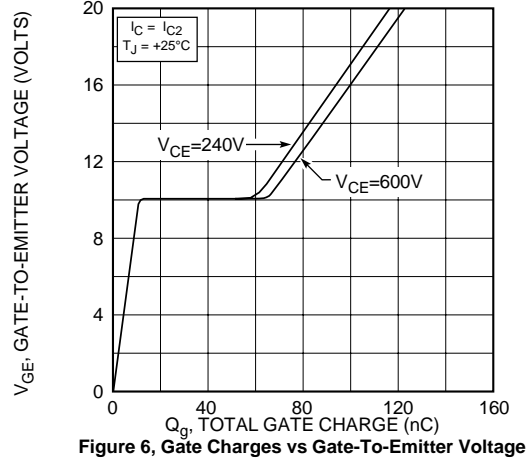
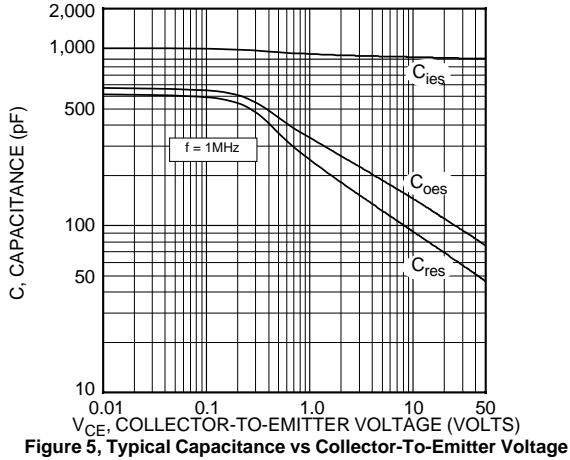
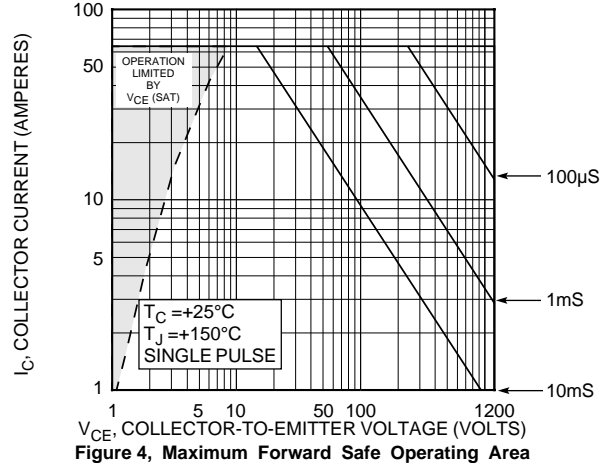
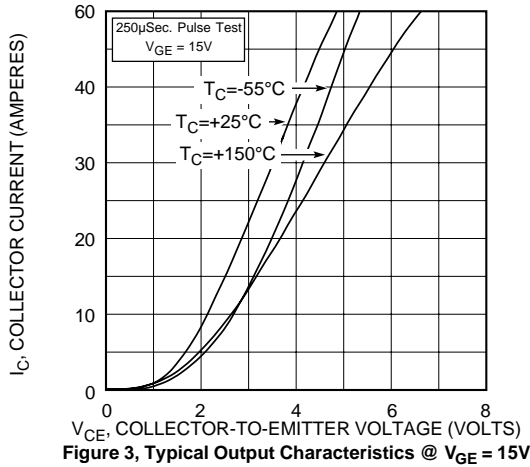
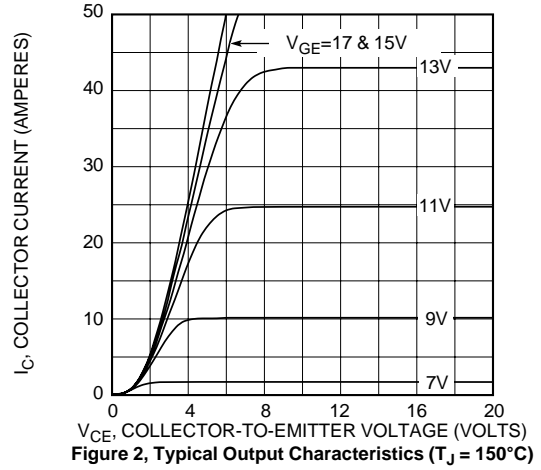
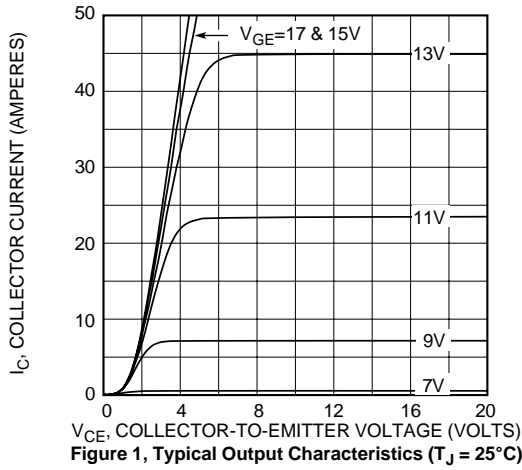
① Repetitive Rating: Pulse width limited by maximum junction temperature.

② I_C = I_{C2}, R_{GE} = 25Ω, L = 110μH, T_J = 25°C

③ See MIL-STD-750 Method 3471

APT Reserves the right to change, without notice, the specifications and information contained herein.

APT20GF120BR



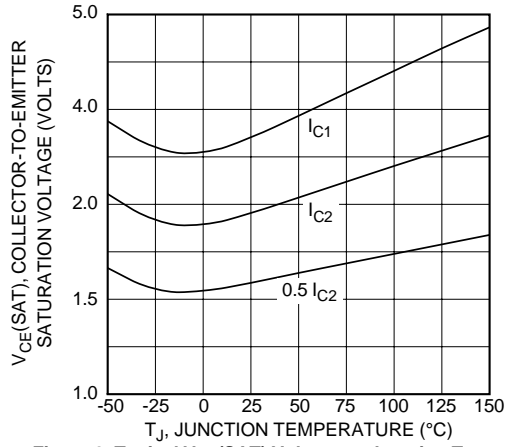


Figure 8, Typical $V_{CE(SAT)}$ Voltage vs Junction Temperature

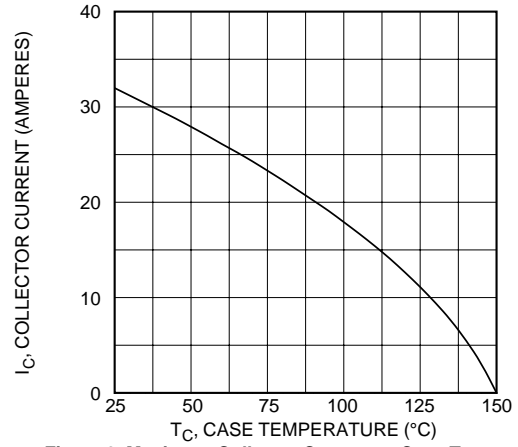


Figure 9, Maximum Collector Current vs Case Temperature

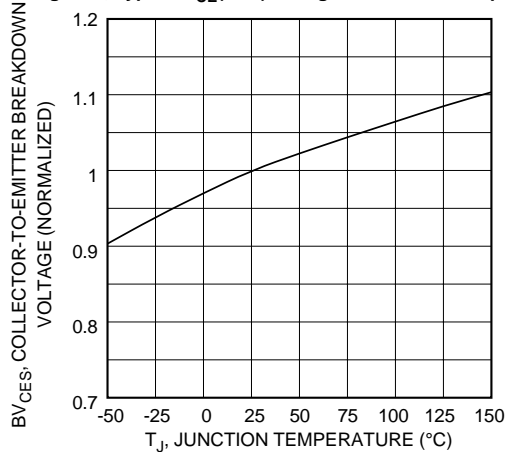


Figure 10, Breakdown Voltage vs Junction Temperature

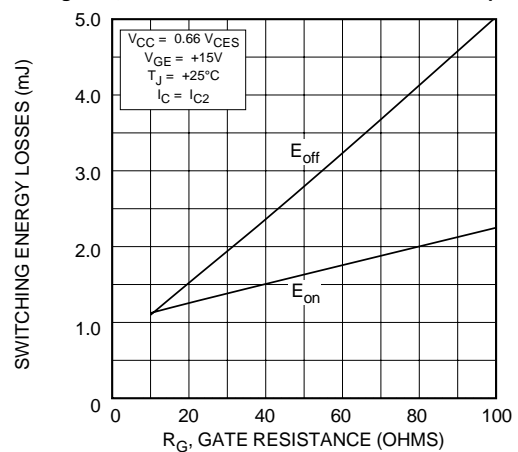


Figure 11, Typical Switching Energy Losses vs Gate Resistance

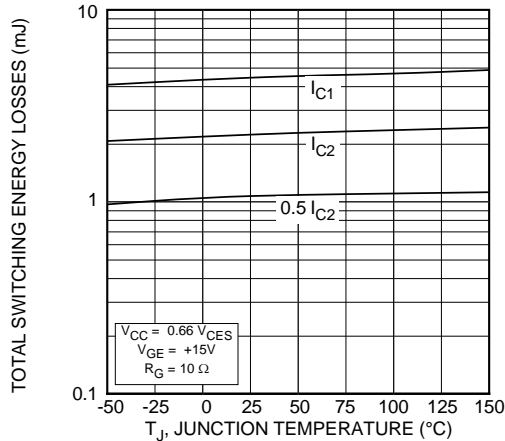


Figure 12, Typical Switching Energy Losses vs. Junction Temperature

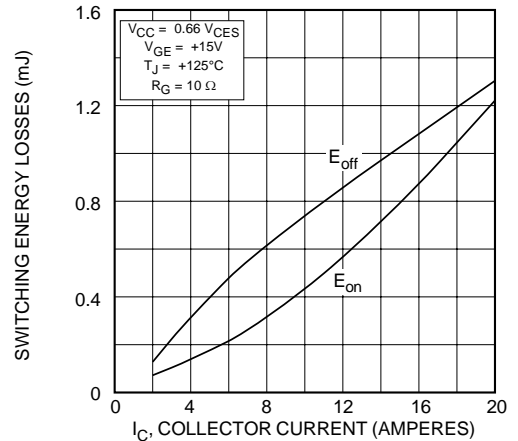


Figure 13, Typical Switching Energy Losses vs Collector Current

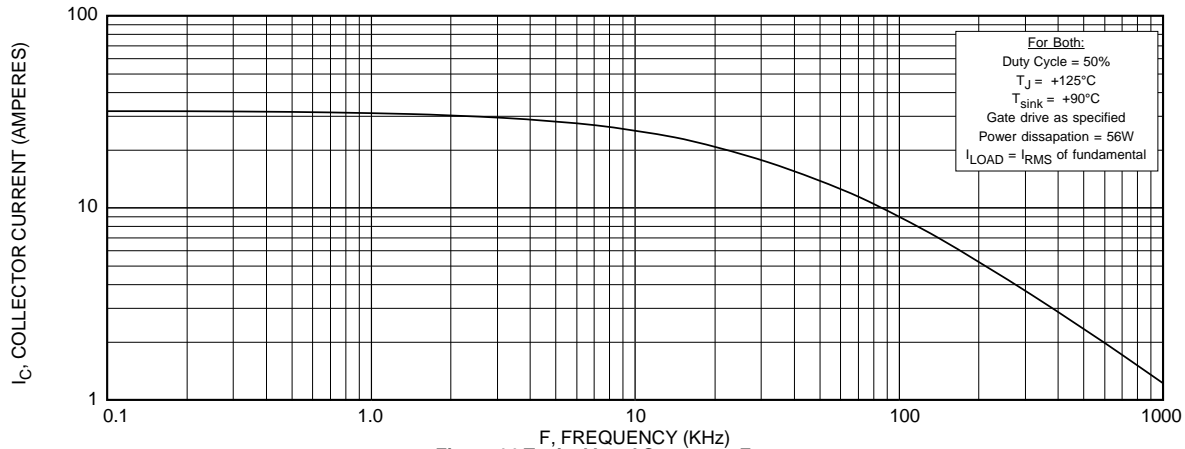


Figure 14, Typical Load Current vs Frequency

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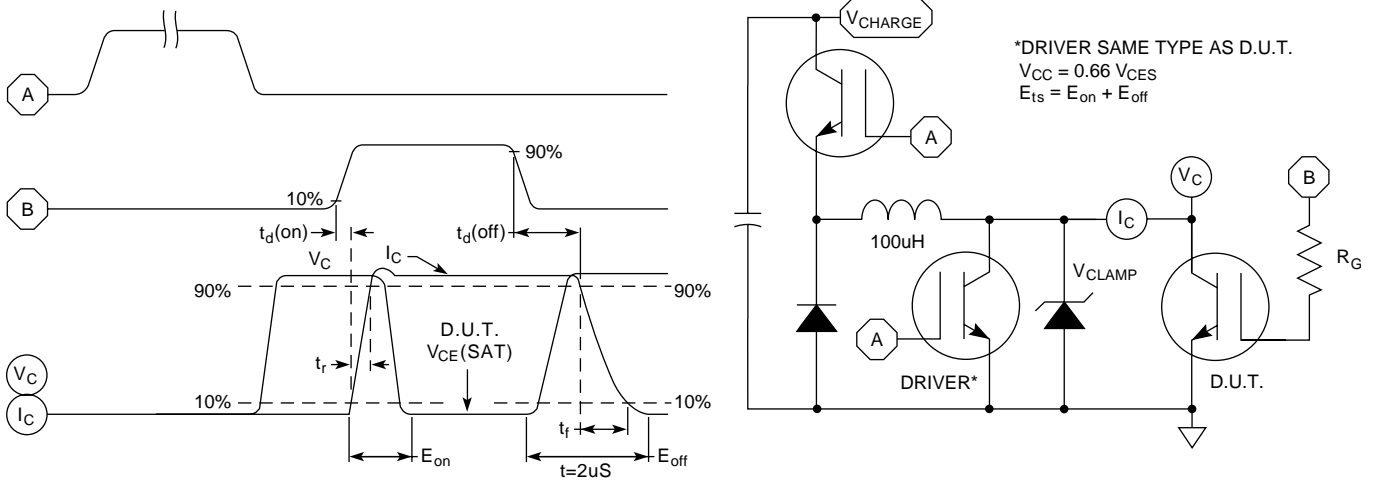


Figure 15, Switching Loss Test Circuit and Waveforms

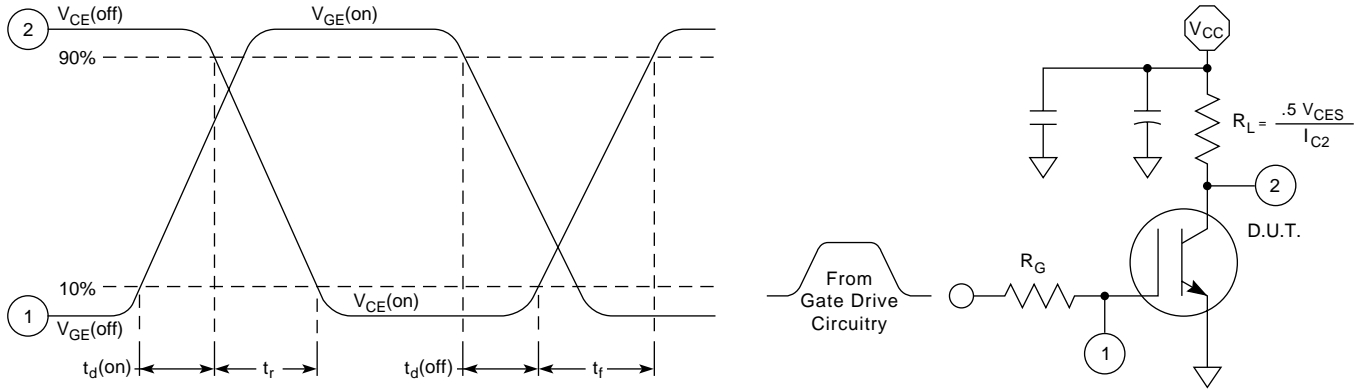
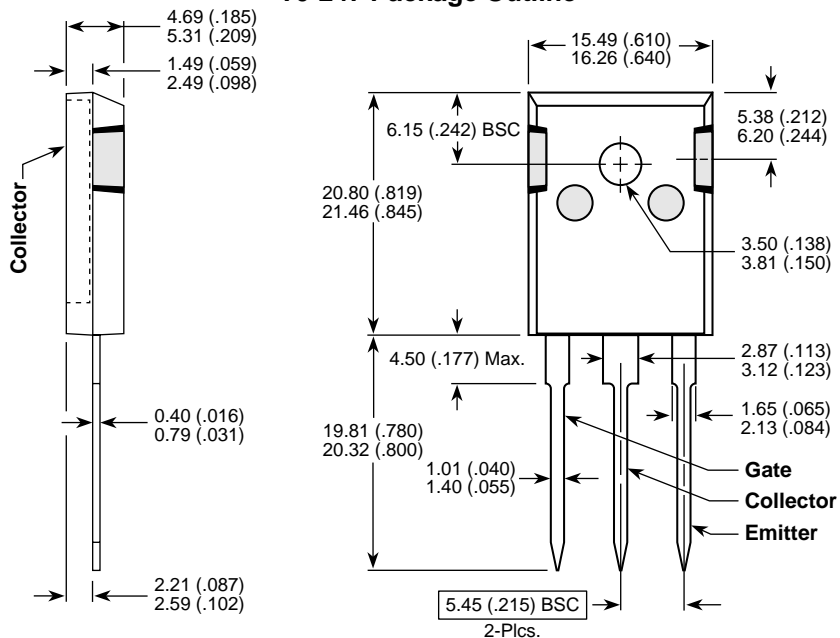


Figure 16, Resistive Switching Time Test Circuit and Waveforms

T0-247 Package Outline



APT's devices are covered by one or more of the following U.S.patents: 4,895,810 5,045,903 5,089,434 5,182,234 5,019,522 5,262,336
 5,256,583 4,748,103 5,283,202 5,231,474 5,434,095 5,528,058

Looking for pricing, stock, or lifecycle information?

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- ⊖ [Microsemi Corporation](#) Information

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- ✓ Excess Inventory Management